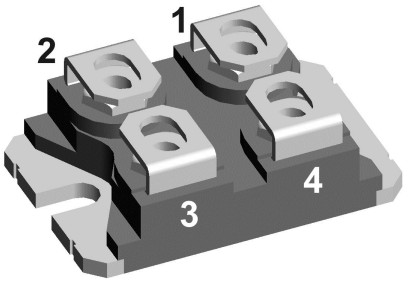
Standard Rectifier

3~ Rectifier		
V_{RRM}	=	1600 V
I_{DAV}	=	150 A
I_{FSM}	=	800 A

Half 3~ Bridge, Common Anode

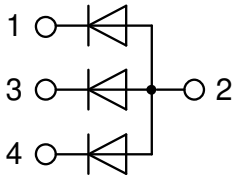
Part number

DMA150YA1600NA



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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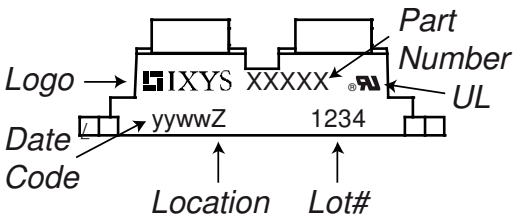
Rectifier

Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1700	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1600	V
I_R	*reverse current*	V_R = 1600 V	T_{VJ} = 25°C			100	µA
		V_R = 1600 V	T_{VJ} = 150°C			1.5	mA
V_F	*forward voltage drop*	I_F = 50 A	T_{VJ} = 25°C			1.21	V
		I_F = 150 A				1.62	V
		I_F = 50 A	T_{VJ} = 125°C			1.16	V
		I_F = 150 A				1.69	V
I_{DAV}	*bridge output current*	T_C = 95°C	T_{VJ} = 150°C			150	A
		rectangular d = ⅓					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.87	V
r_F	*slope resistance* }					5.6	mΩ
R_{thJC}	*thermal resistance junction to case*					0.6	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.1		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			165	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			800	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			865	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			680	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			735	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			3.20	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			3.12	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			2.31	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.25	kA²s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		27		pF

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Package SOT-227B (minibloc)					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					150	A
T_{VJ}	*virtual junction temperature*				-40		150	°C
T_{op}	*operation temperature*				-40		125	°C
T_{stg}	*storage temperature*				-40		150	°C
Weight						30		g
M_D	*mounting torque*				1.1		1.5	Nm
M_T	*terminal torque*				1.1		1.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	10.5	3.2			mm
$d_{Spb/Apb}$			*terminal to backside*	8.6	6.8			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		3000			V
		t = 1 minute			2500			V

Product Marking



Part description

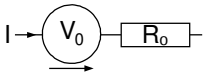
D = Diode
M = Standard Rectifier
A = (up to 1800V)
150 = Current Rating [A]
YA = Half 3~ Bridge, Common Anode
1600 = Reverse Voltage [V]
NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA150YA1600NA	DMA150YA1600NA	Tube	10	509181

Similar Part	Package	Voltage class
DMA150YC1600NA	SOT-227B (minibloc)	1600

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150°C

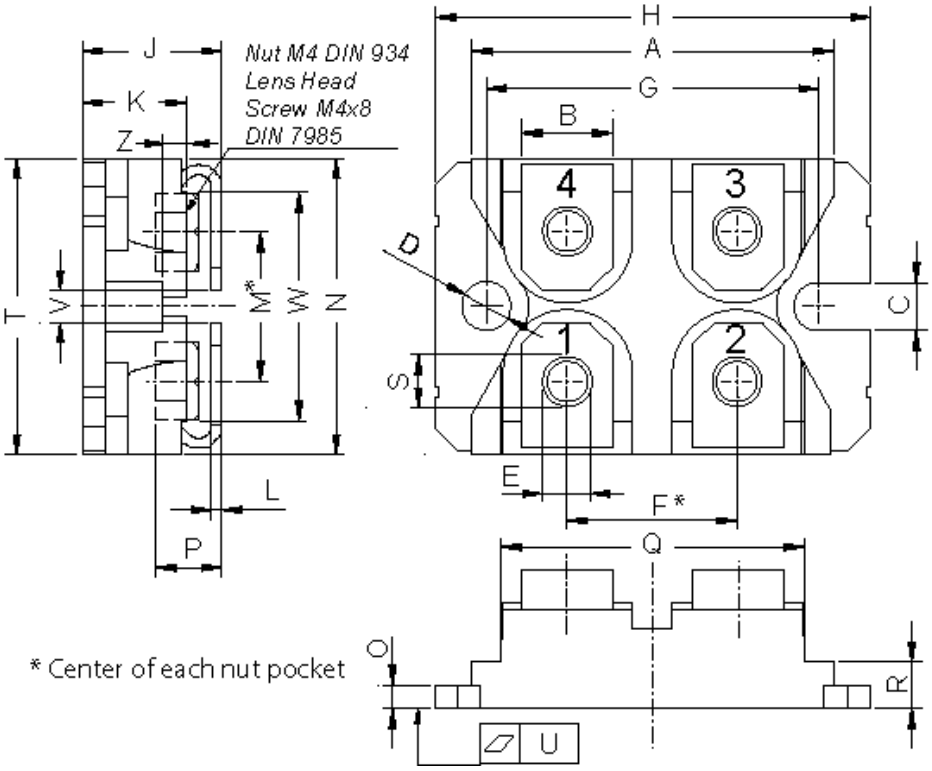


Rectifier

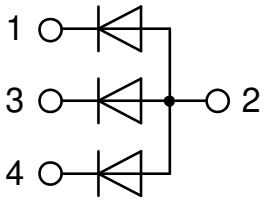
$V_{0\ max}$	*threshold voltage*	0.87	V
$R_{0\ max}$	*slope resistance **	4.4	mΩ

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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



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Rectifier

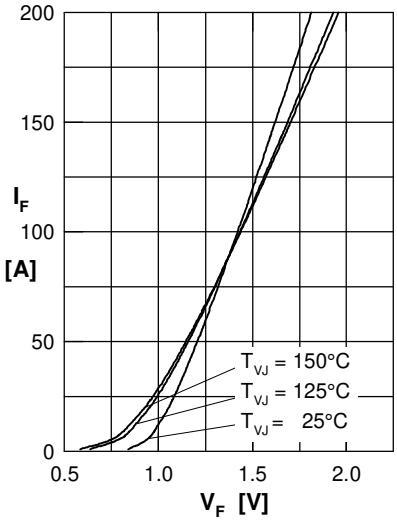


Fig. 1 Forward current versus voltage drop per diode

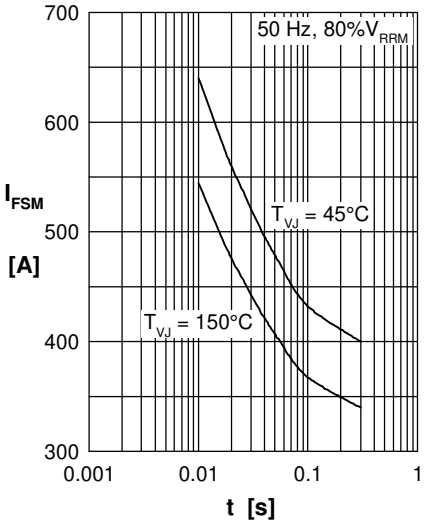


Fig. 2 Surge overload current vs. time per diode

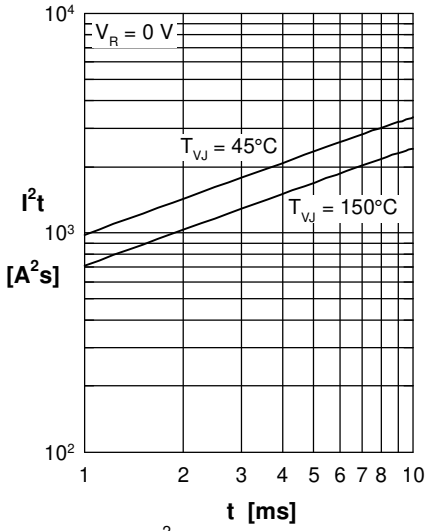


Fig. 3 I^2t versus time per diode

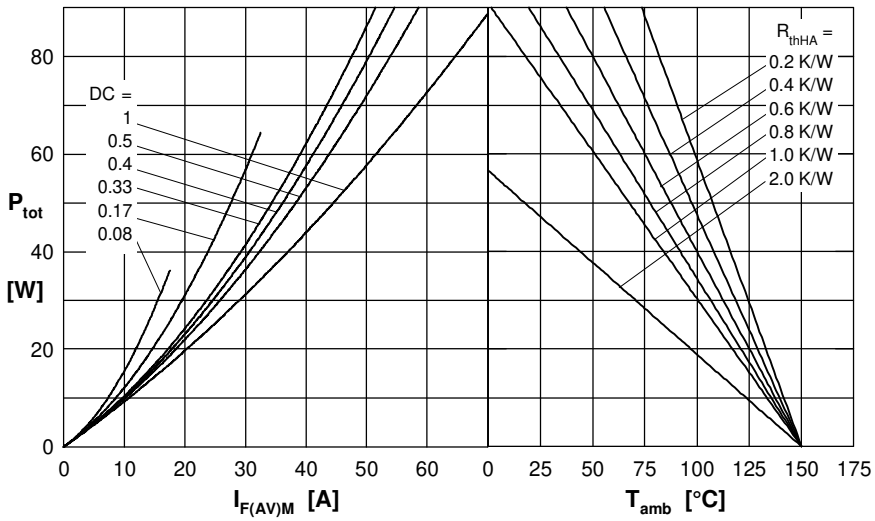


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

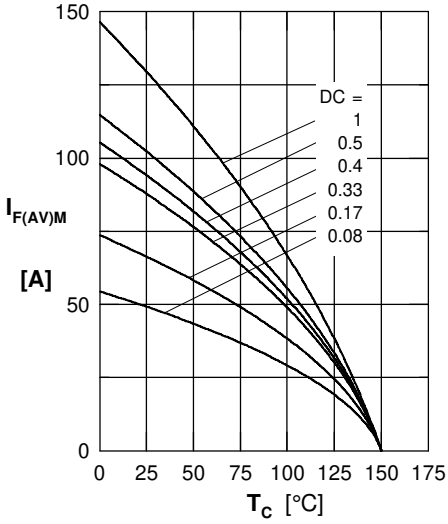


Fig. 5 Max. forward current vs. case temperature per diode

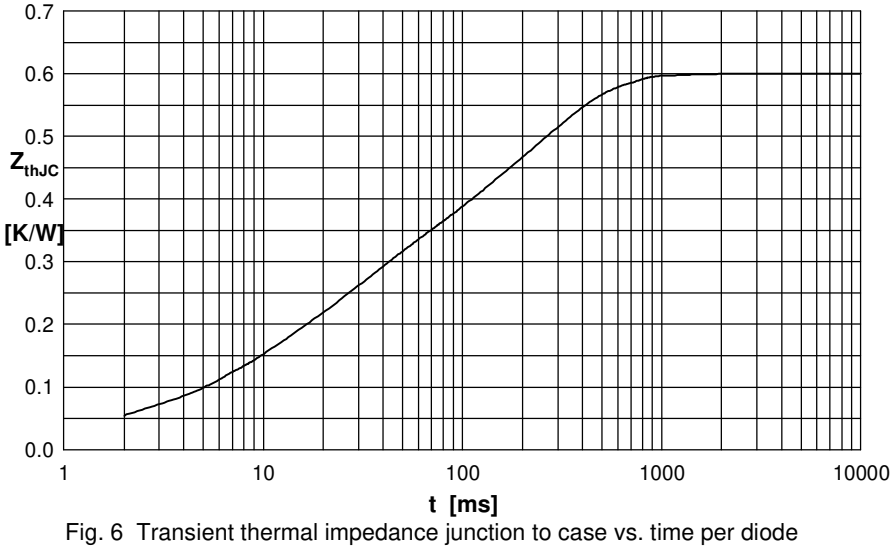


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0240	0.01000
2	0.0160	0.00001
3	0.0500	0.00500
4	0.1800	0.02300
5	0.3300	0.22000

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